

on request

Standard Rectifier Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

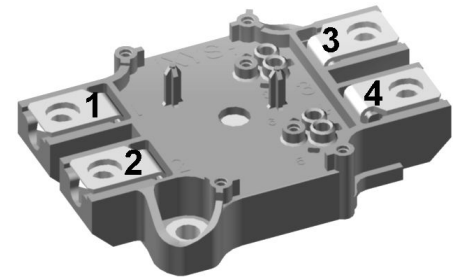
$$I_{FAV} = 200 \text{ A}$$

$$V_F = 1.06 \text{ V}$$


Phase leg

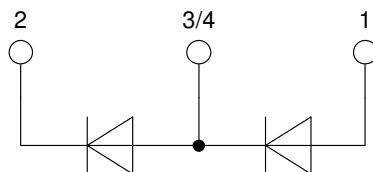
Part number

MDMA200P1600SA



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: SimBus A

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Gate: Spring contacts for solder-free PCB-mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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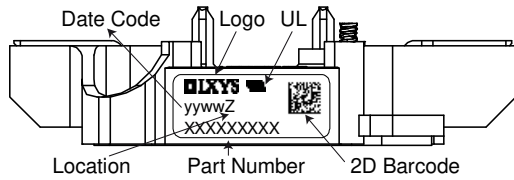
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V
V_{RRM}	max. repetitive reverse blocking voltage					1600	V
I_R	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		200	μA
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		15	mA
V_F	forward voltage drop	$I_F = 200$ A		$T_{VJ} = 25^\circ\text{C}$		1.13	V
						$I_F = 400$ A	
		$I_F = 200$ A		$T_{VJ} = 125^\circ\text{C}$		1.06	V
						$I_F = 400$ A	
I_{FAV}	average forward current	$T_C = 110^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		200	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.76	V
r_F	slope resistance					1.4	m Ω
R_{thJC}	thermal resistance junction to case					0.15	K/W
R_{thCH}	thermal resistance case to heatsink				0.08		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		830	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		6.00	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		6.48	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		5.10	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		5.51	kA
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		180.0	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		174.7	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		130.1	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		126.3	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		273	pF



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Package SimBus A		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			300	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				152		g
M_D	mounting torque		3		5	Nm
M_T	terminal torque		2.5		5	Nm
$d_{Spp/Apb}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	14.0	10.0		mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



Part description

- M = Module
- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 200 = Current Rating [A]
- P = Phase leg
- 1600 = Reverse Voltage [V]
- SA = SimBus A

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA200P1600SA	MDMA200P1600SA	Blister	9	510373

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Rectifier

$V_{0\ max}$	threshold voltage	0.76	V
$R_{0\ max}$	slope resistance *	0.8	mΩ

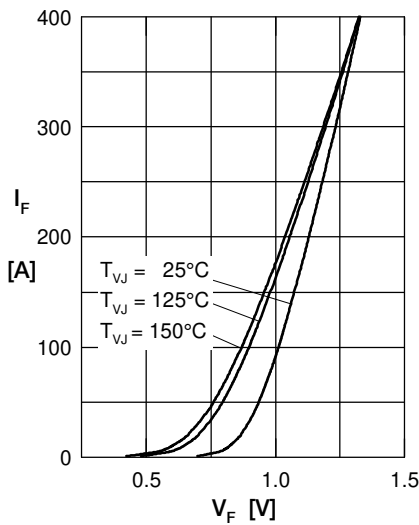
Rectifier


Fig. 1 Forward current versus voltage drop per diode

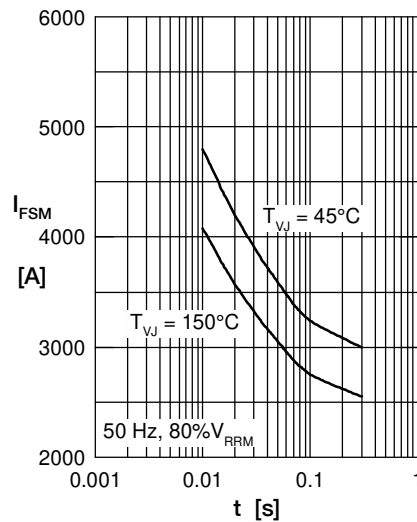


Fig. 2 Surge overload current vs. time per diode

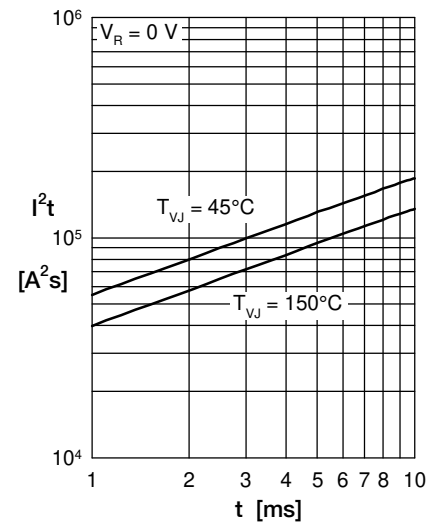
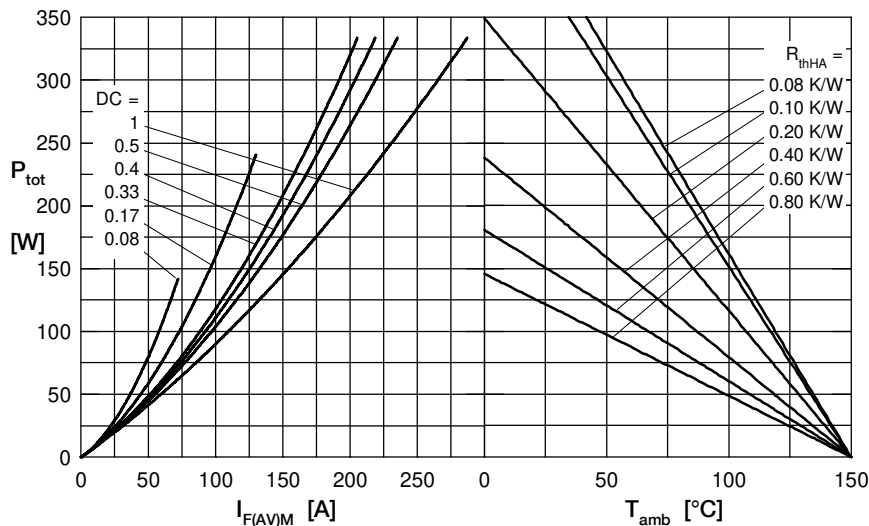

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

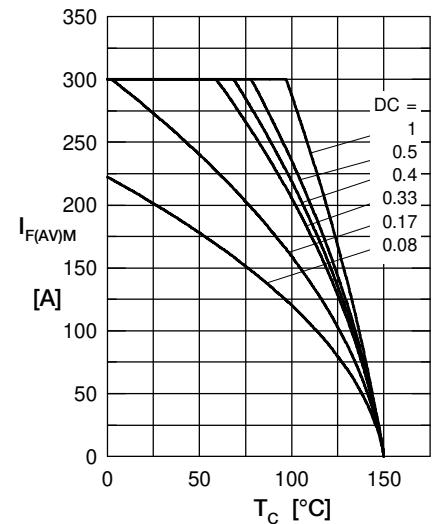


Fig. 5 Max. forward current vs. case temperature per diode

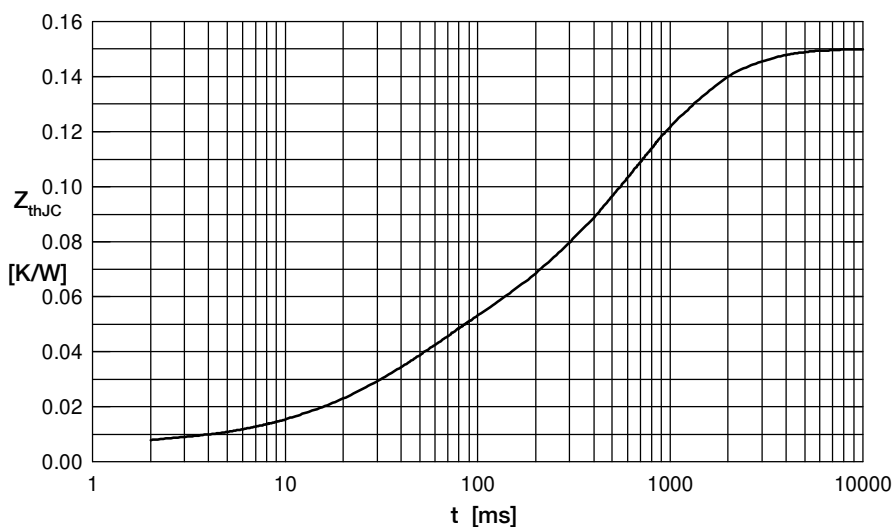


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.006	0.0005
2	0.035	0.0400
3	0.079	0.5500
4	0.030	1.5000

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